

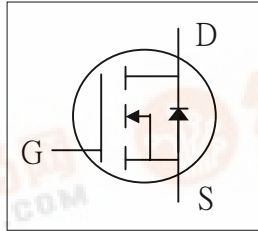
# AP09N90W



**Advanced Power  
Electronics Corp.**

*N-CHANNEL ENHANCEMENT MODE  
POWER MOSFET*

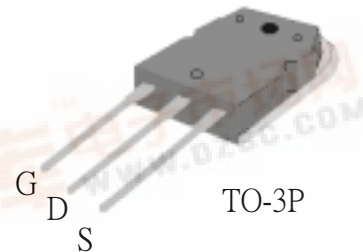
- ▼ Repetitive Avalanche Rated
- ▼ Fast Switching
- ▼ Simple Drive Requirement



$BV_{DSS}$	900V
$R_{DS(ON)}$	1.2Ω
$I_D$	8.6A

## Description

AP09N90 series are specially designed as main switching devices for universal 90~265VAC off-line AC/DC converter applications. TO-3P type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	900	V
$V_{GS}$	Gate-Source Voltage	± 30	V
$I_D @ T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	8.6	A
$I_D @ T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	30	A
$P_D @ T_C=25^{\circ}C$	Total Power Dissipation	240	W
	Linear Derating Factor	1.92	W/°C
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	92	mJ
$I_{AR}$	Avalanche Current	5.2	A
$E_{AR}$	Repetitive Avalanche Energy	8.6	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Thermal Resistance Junction-case	Max. 0.52	°C/W
Rthj-a	Thermal Resistance Junction-ambient	Max. 40	°C/W





**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =1mA	900	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.67	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4.5A	-	-	1.2	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	-	4	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =4.5A	-	11.5	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =900V, V <sub>GS</sub> =0V	-	-	10	uA
	Drain-Source Leakage Current (T <sub>j</sub> =150°C)	V <sub>DS</sub> =720V, V <sub>GS</sub> =0V	-	-	100	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> = ± 30V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>3</sup>	I <sub>D</sub> =8.6A	-	67.1	120	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =540V	-	17	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =10V	-	19.9	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>3</sup>	V <sub>DD</sub> =450V	-	25.8	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =5A	-	10.3	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =10Ω, V <sub>GS</sub> =10V	-	305.2	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =90Ω	-	536	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	4087	6000	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	221	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	51	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I <sub>S</sub>	Continuous Source Current ( Body Diode )	V <sub>D</sub> =V <sub>G</sub> =0V , V <sub>S</sub> =1.5V		-	8.6	A
I <sub>SM</sub>	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	30	A
V <sub>SD</sub>	Forward On Voltage <sup>3</sup>	T <sub>j</sub> =25°C, I <sub>S</sub> =8.6A, V <sub>GS</sub> =0V	-	-	1.5	V

**Notes:**

- 1.Pulse width limited by safe operating area.
- 2.Starting T<sub>j</sub>=25°C , V<sub>DD</sub>=50V , L=6.8mH , R<sub>G</sub>=25Ω , I<sub>AS</sub>=5.2A.
- 3.Pulse width ≤300us , duty cycle ≤2%.

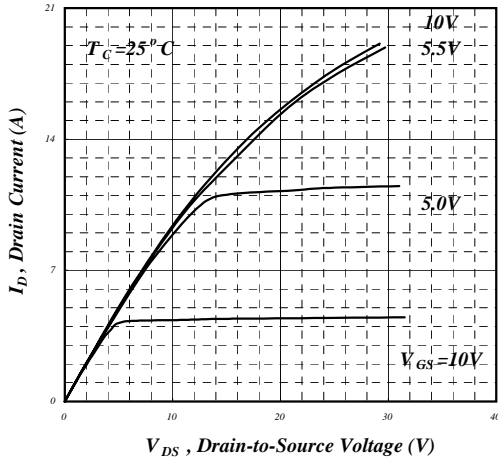


Fig 1. Typical Output Characteristics

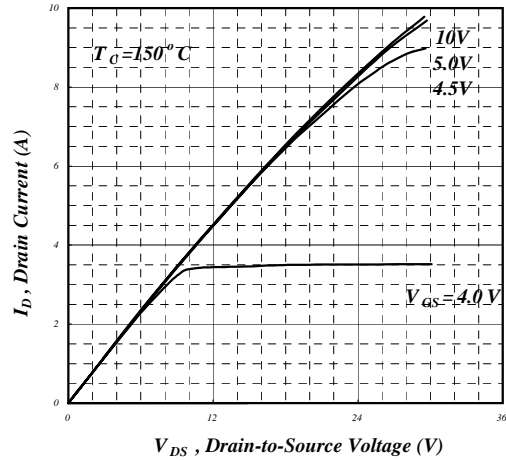


Fig 2. Typical Output Characteristics

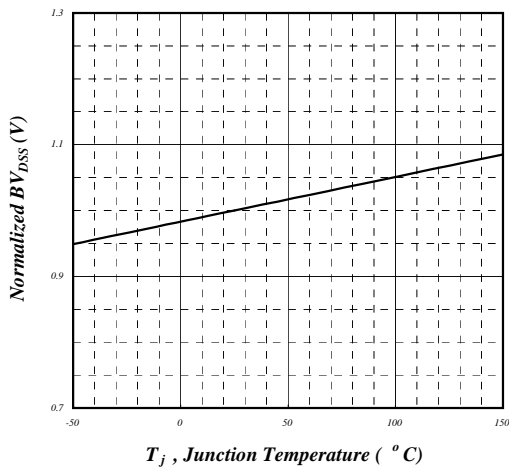


Fig 3. Normalized  $BV_{DSS}$  v.s. Junction

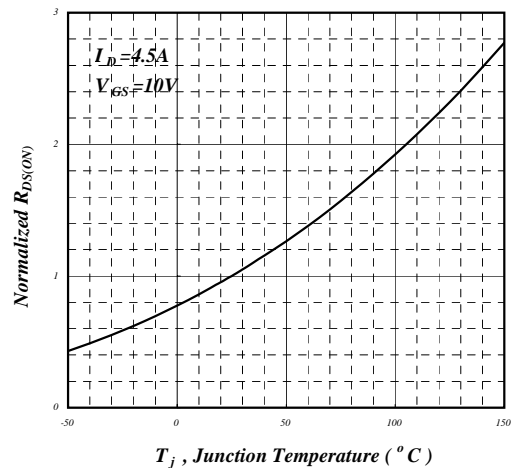


Fig 4. Normalized On-Resistance

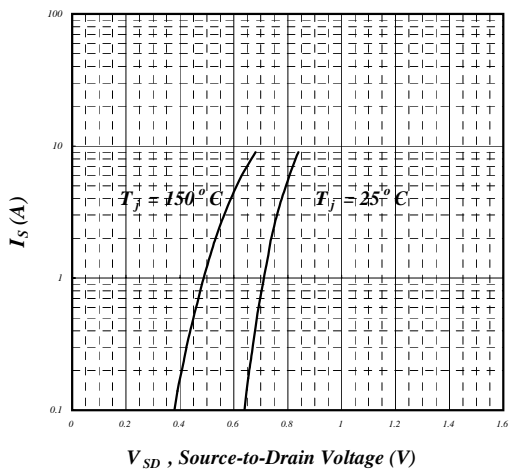


Fig 5. Forward Characteristic of Reverse Diode

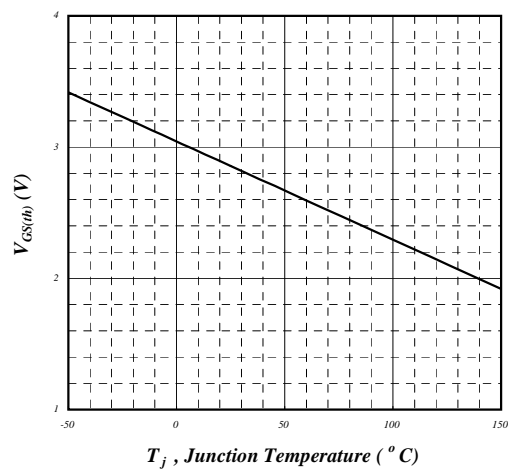


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

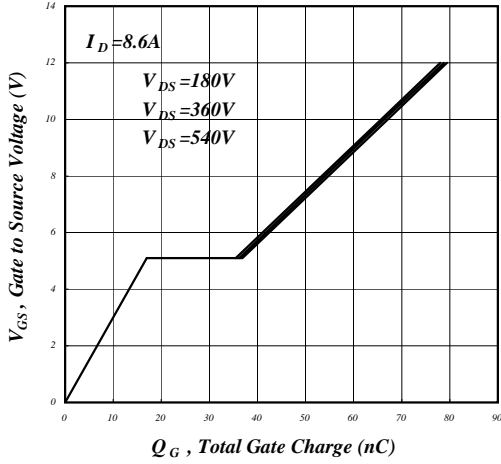


Fig 7. Gate Charge Characteristics

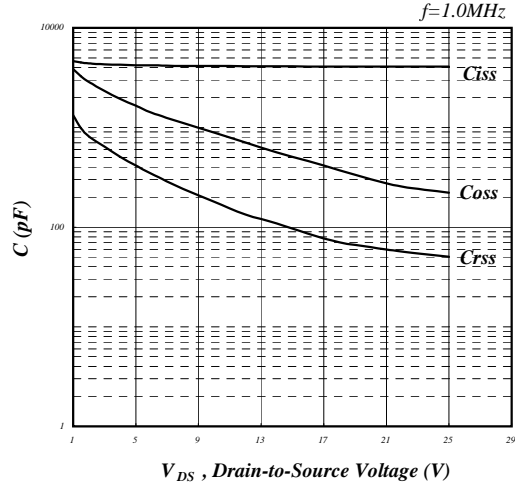


Fig 8. Typical Capacitance Characteristics

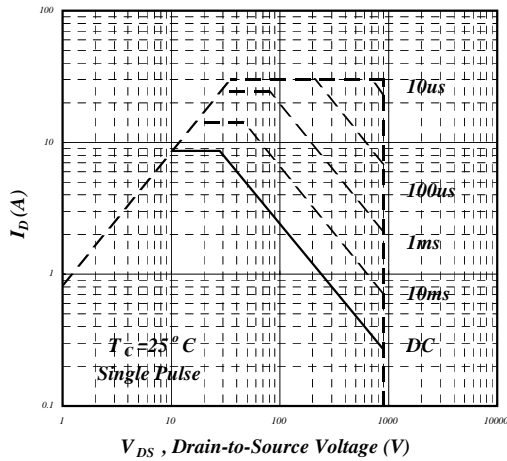


Fig 9. Maximum Safe Operating Area

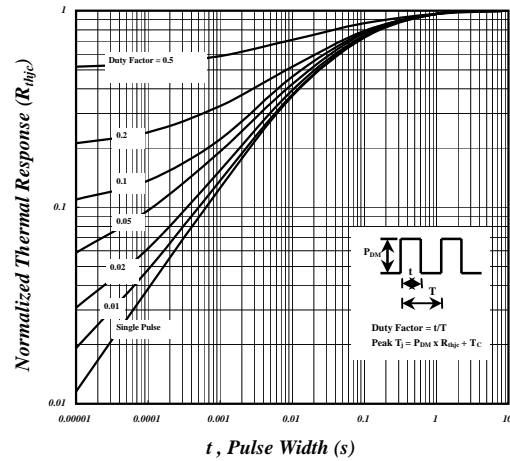


Fig 10. Effective Transient Thermal Impedance

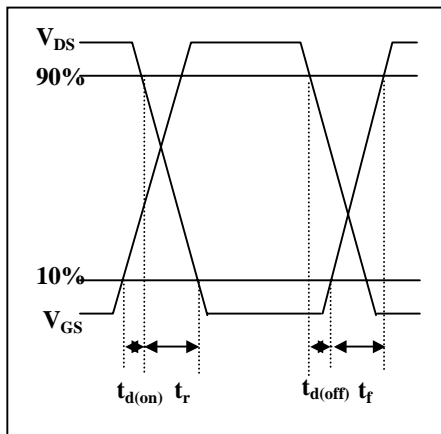


Fig 11. Switching Time Waveform

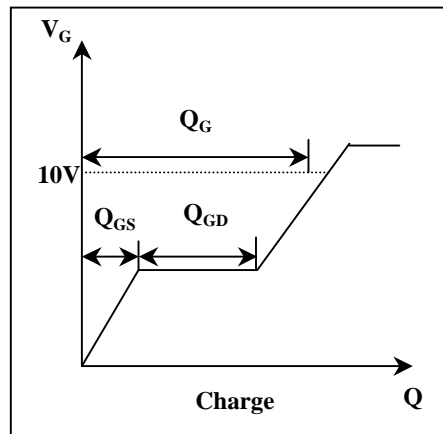


Fig 12. Gate Charge Waveform